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(54) **IN-PLANE-SWITCHING-MODE LIQUID CRYSTAL DISPLAY DEVICE**

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G02F 1/1343 (2006.01)

(52) **U.S. Cl.** **349/141**; 349/138

(58) **Field of Classification Search** 349/141
See application file for complete search history.

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(57) **ABSTRACT**

An IPS-mode LCD device includes a TFT substrate and a counter substrate sandwiching therebetween a LC layer. Each pixel includes a pixel electrode covered by a passivation film formed on the TFT substrate, and a common electrode formed on the top surface of the passivation film. The passivation film has a first thickness at a portion in contact with the common electrode and a second thickness smaller than the first thickness at a portion in contact with the pixel electrode, thereby having a flat top surface of the passivation film.

8 Claims, 8 Drawing Sheets

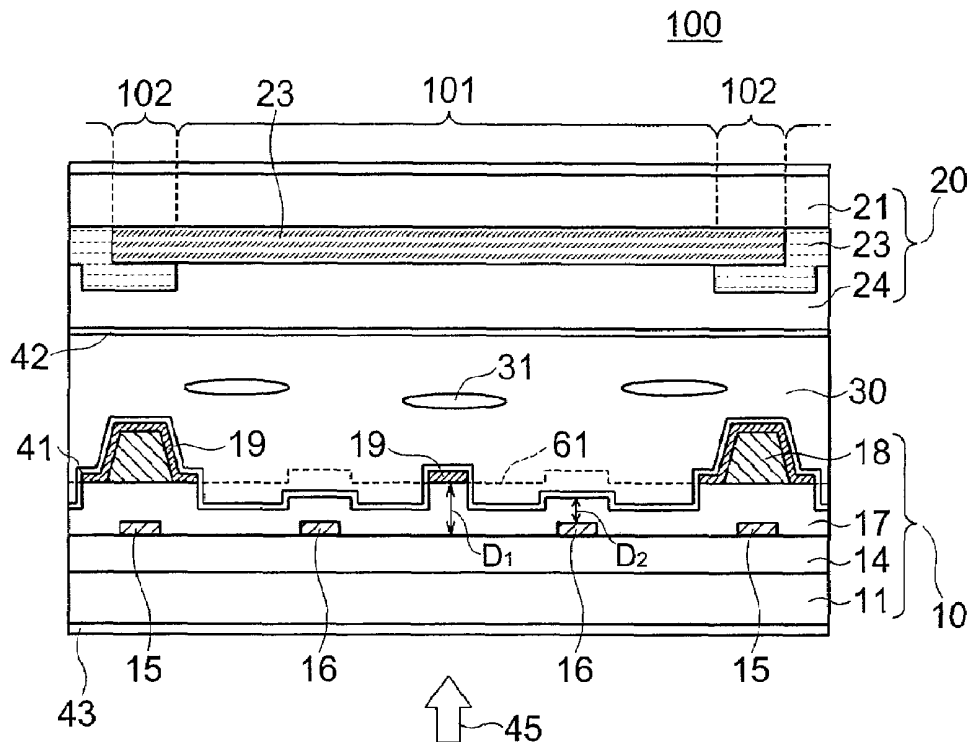


FIG. 2

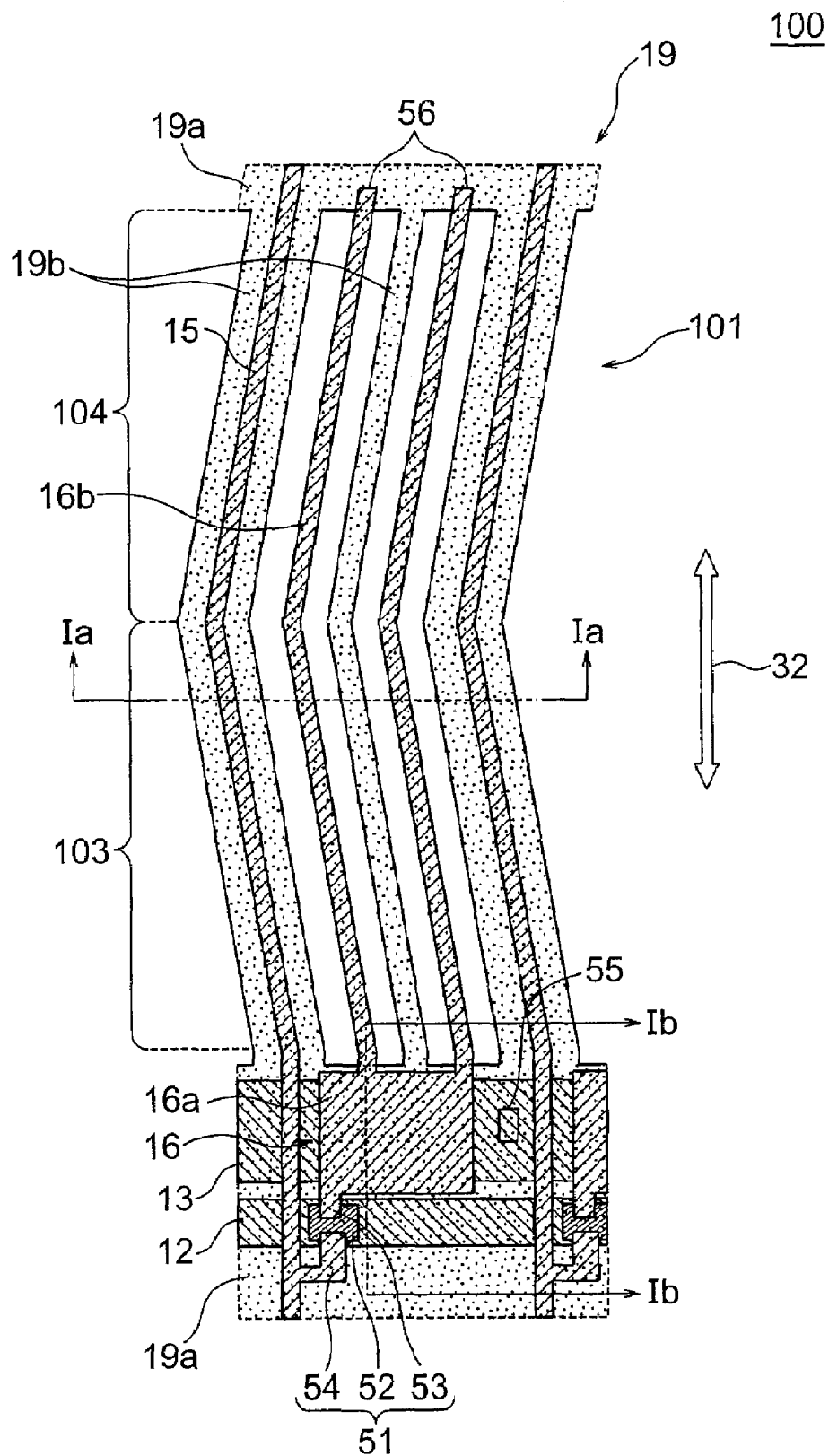


FIG. 3A

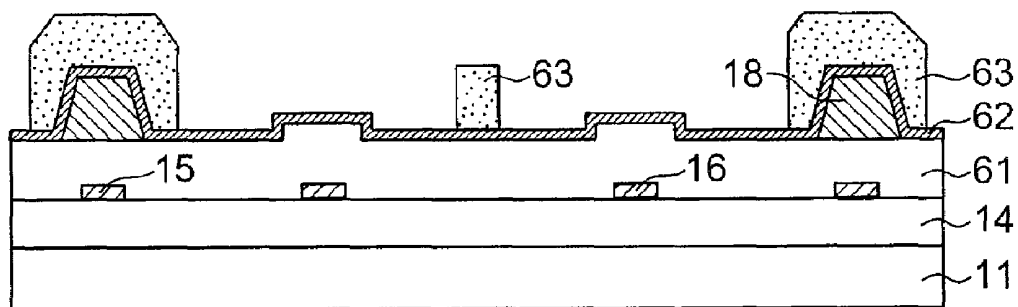


FIG. 3B

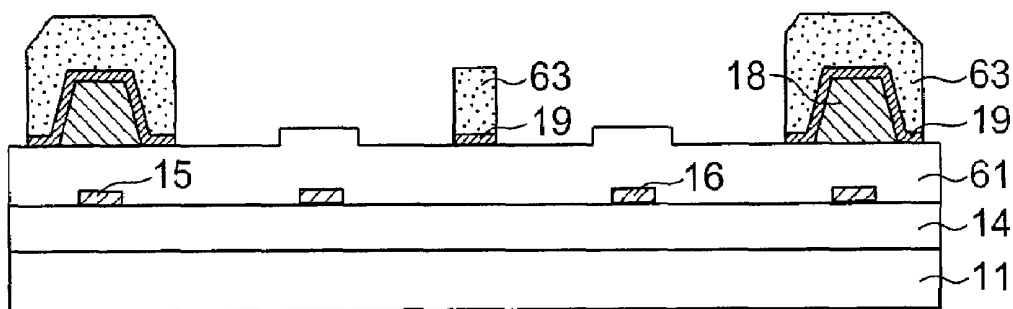


FIG. 3C

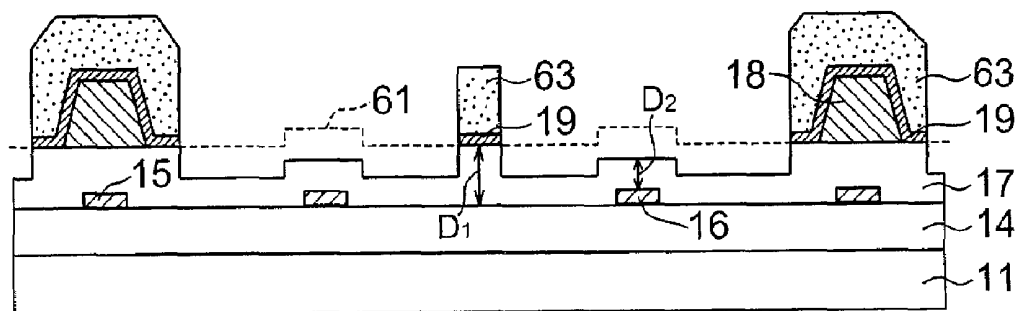


FIG. 4

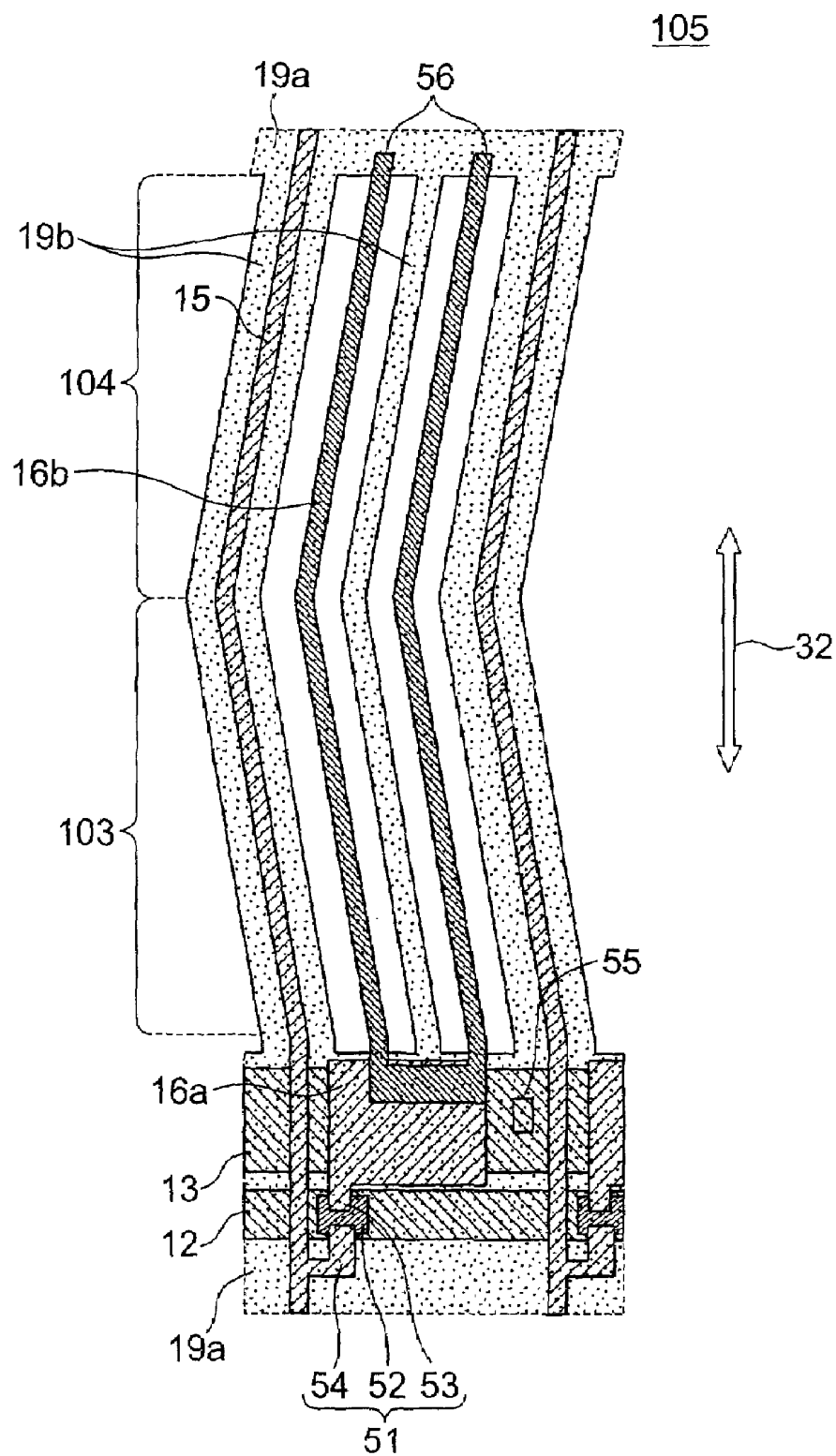


FIG. 5A

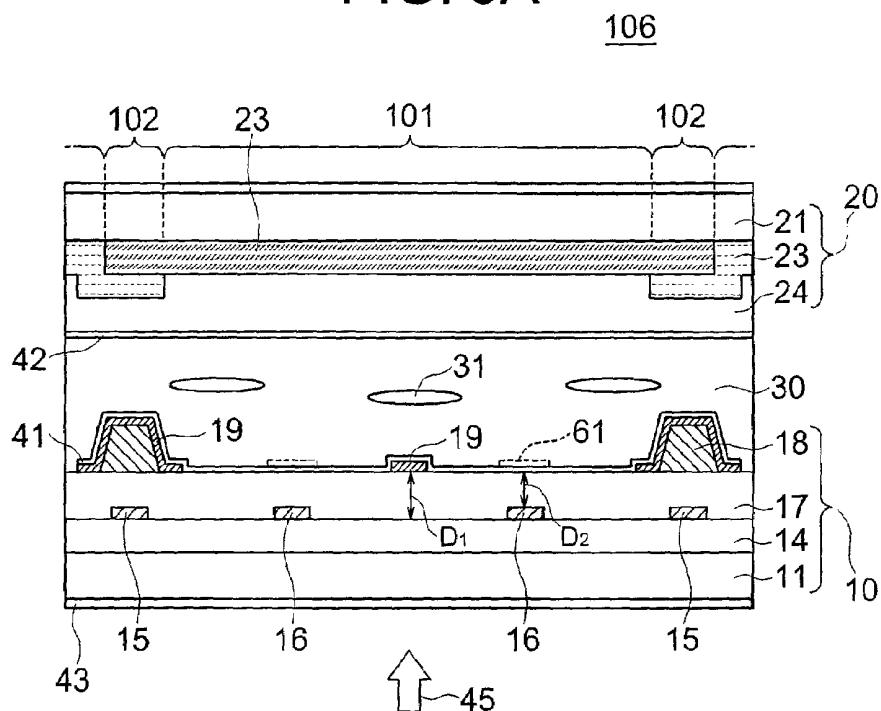


FIG. 5B

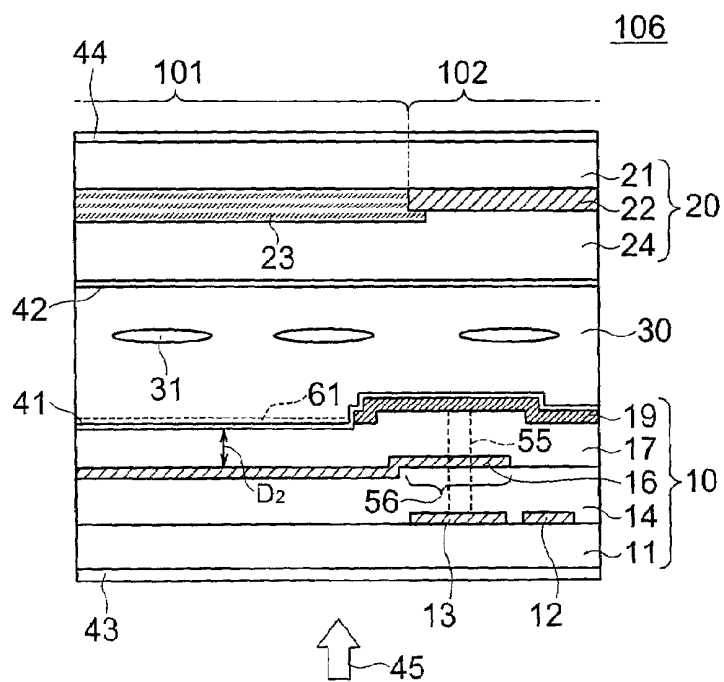


FIG. 6A

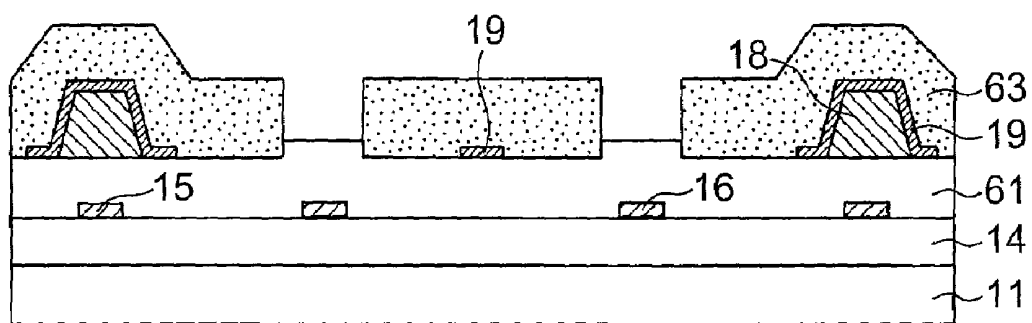


FIG. 6B

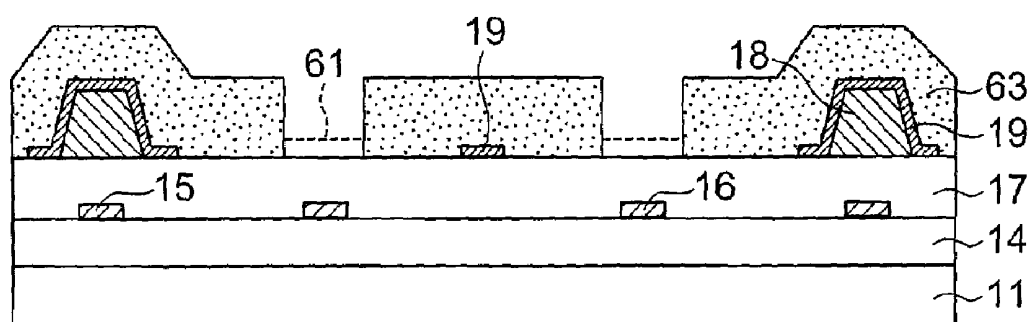


FIG. 7
PRIOR ART

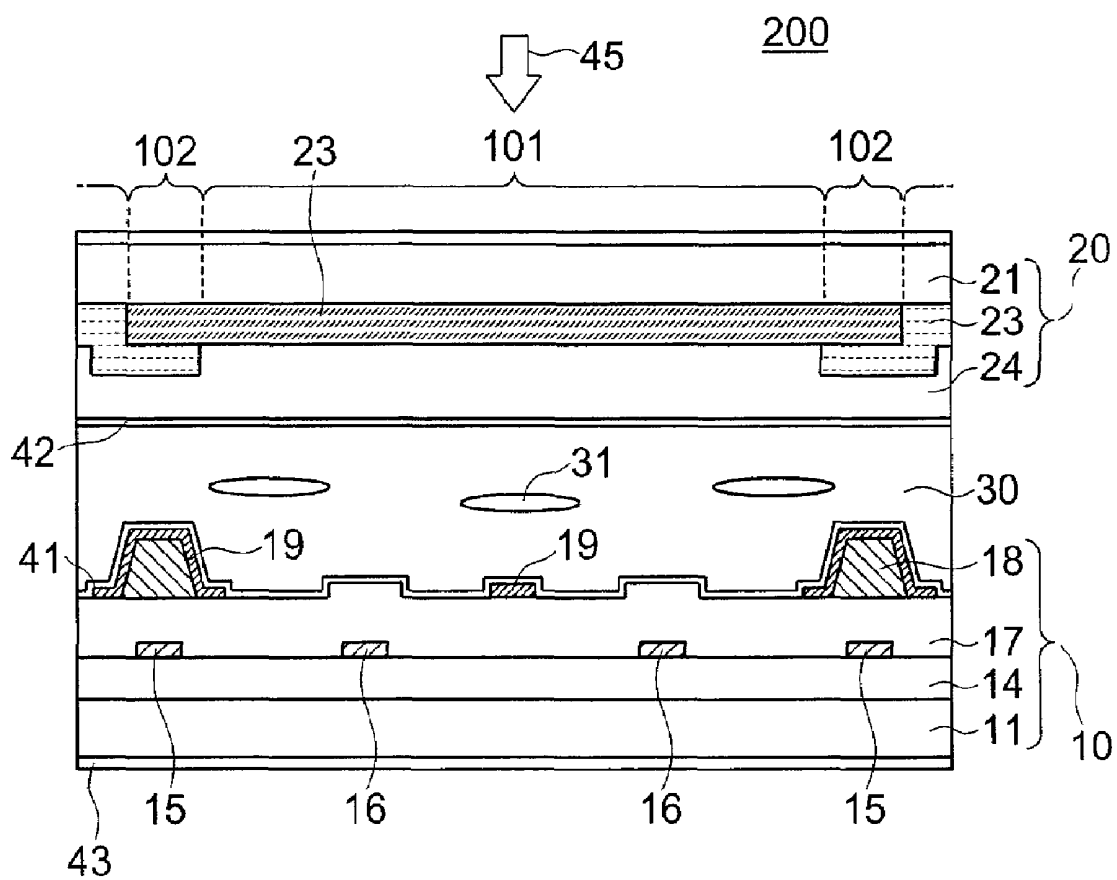


FIG. 8A

PRIOR ART

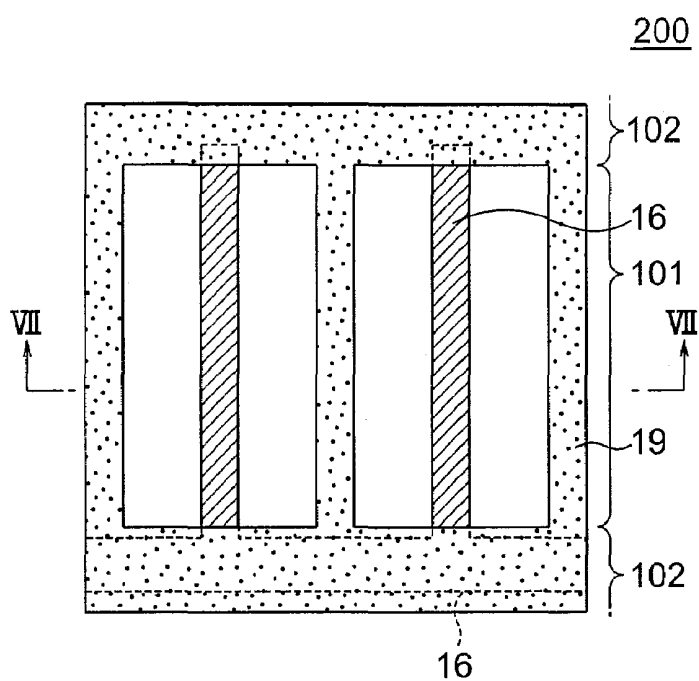
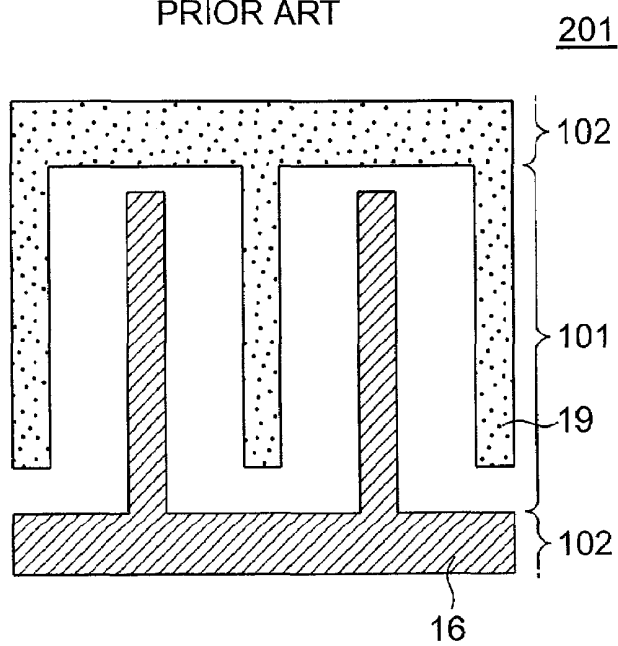


FIG. 8B

PRIOR ART



IN-PLANE-SWITCHING-MODE LIQUID CRYSTAL DISPLAY DEVICE

BACKGROUND OF THE INVENTION

(a) Field of the Invention

The present invention relates to an in-plane-switching-mode (IPS-mode) liquid crystal display (LCD) device and, more particularly, to an IPS-mode LCD device having a uniform electric field in each pixel. The present invention also relates to a method for manufacturing a LCD device.

(b) Description of the Related Art

The LCD devices are categorized into two modes including: a first mode wherein orientation of liquid crystal (LC) molecules in the LC layer is rotated in the direction normal to the surface of the substrates sandwiching therebetween the LC layer; and a second mode wherein orientation of LC molecules are rotated in the direction parallel to the surface of the substrates (substrate surface). The first modes include a twisted-nematic-mode (TN-mode) LCD device as a typical example, and the second modes include an IPS-mode LCD device as a typical example.

In the TN-mode LCD device, since the LC molecules are rotated and deviated from the plane normal to the substrate surface, the polarization angle of the light passed by the LC layer deviates along with the increase of the viewing angle to achieve only a limited viewing angle characteristic. On the other hand, in the IPS-mode LCD device, since the LC molecules are rotated in the plane normal to the substrate surface, polarization angle of the light does not change even with a larger viewing angle, to thereby achieve a wider viewing angle characteristic. Thus, an increased number of 10 IPS-mode LCD devices are employed.

It is noted here that the IPS-mode LCD devices include a first type wherein a pair of electrodes in each pixel are disposed on the common surface of an insulation film, and a second type wherein the pair of electrodes in each pixel are disposed on opposite surfaces of an insulation film. The second-type LCD device is shown in FIG. 7.

The LCD device of FIG. 7 includes a thin-film-transistor (TFT) substrate 10 disposed on the light-incident side of the LC layer 30 and a counter substrate 20 disposed on the light 20 emitting side of the LC layer 30. The TFT substrate 10 includes a passivation film 17 having a bottom surface on which a common electrode 19 is formed and a top surface on which a pixel electrode 16 is formed.

FIG. 8A shows an arrangement of the pixel electrode 16 25 and common electrode 19 in a pixel of the LCD device of FIG. 7. FIG. 7 corresponds to a sectional view taken along line VII-VII in FIG. 8A. The pixel electrode 16 and common electrode 19 oppose each other in the lateral direction of the pixel in FIG. 8A. Since the pixel electrode 16 and common electrode 19 sandwich therebetween the passivation film 17, as described above, both the electrodes 19 and 16 may overlap each other as viewed normal to the substrate surface.

FIG. 8B shows a pixel of the first-type IPS-mode LCD device, generally designated by numeral 201, wherein both the pixel electrode 16 and common electrode 19 are formed on the common surface of an insulation film. In the structure of FIG. 8B, the pixel electrode 16 and common electrode 19 have therebetween a specific gap as viewed normal to the substrate surface for avoiding a short-circuit failure

The structure of FIG. 8A has an advantage that the pixel electrode 16 has a larger capacitance with respect to the common electrode 19, which improves the charge storage capability thereof. The structure of FIG. 8A has another advantage that the lateral electric field applied to the LC layer

increases in the vicinity of the edge of the electrodes 16, 19, thereby increasing a light transmission factor during display of a bright state.

The arrangement of the LCD device such as shown in 25 FIGS. 7 and 8A is described in Patent Publication JP-2004-62145A, for example.

In the LCD device 200 of FIG. 7, the passivation film 17 should have an insulation function sufficient to withstand the voltage between the pixel electrode 16 and the common electrode 19. If the thickness of the passivation film 17 has a wide range of variation, and thus has a thickness in a pixel or pixels below a required range for withstanding a voltage applied between the pixel electrode 16 and the common electrode 19, a breakdown of the passivation film 17 will result in the pixel or pixels suffering a defect known as "a point defect" in the LCD device.

On the other hand, if the passivation film 17 has a thickness greater than the required range, the voltage to be applied to the LC layer 30 is reduced by the passivation films 17, whereby the passivation film 17 may prevent a sufficient lateral electric field from being applied to the LC layer 30. For avoiding such a scenario to impact the lateral electric field, higher voltage must be applied between the pixel electrode 16 and the common electrode 19, which increases the power dissipation of the LCD device.

In addition, the passivation film 17 having a larger thickness provides a wider range of variation in the lateral electric field applied to the LC layer 30. This variation causes a wider range of variation in the storage function for the electric charge among the pixels, which may create a flicker or residual image in the LCD device.

SUMMARY OF THE INVENTION

In view of the above problems in the conventional techniques, it is an object of the present invention to provide an IPS-mode LCD device which is capable of assuring a suitable withstand voltage between the electrodes in the pixels, reducing the power dissipation of the LCD device, and suppressing the flicker or residual image in the LCD device.

The present invention provides a liquid crystal display (LCD) device including a liquid crystal (LC) layer, and first and second substrates sandwiching therebetween the LC layer to define a plurality of pixels, the first substrate including a first electrode and a second electrode in each of the pixels to apply the LC layer with a lateral electric field, wherein: the first substrate mounts thereon a transparent insulation film; the first electrode is formed on a first surface of the transparent insulation film near the LC layer, the second electrode is formed on a second surface of the transparent insulation film far from the LC layer; and the transparent insulation film has a first thickness (D1) at a location in contact with the first electrode, and a second thickness (D2) smaller than the first thickness at a location in contact with the second electrode.

The present invention provides a method for fabricating a liquid crystal display (LCD) device including a liquid crystal (LC) layer, and first and second substrates sandwiching therebetween the LC layer to define a plurality of pixels, the first substrate including a first electrode and a second electrode in each of the pixels to apply the LC layer with a lateral electric field, the method including the steps of: forming the second electrode on the first substrate; forming a transparent insulation film on the second electrode; forming a transparent conductive film on the transparent insulation film; forming a mask pattern having a first thickness (D1) on the transparent conductive film; patterning the transparent conductive film by

using the mask pattern as an etching mask to form the first electrode; and selectively etching the transparent insulation film by using the mask pattern as an etching mask to obtain a first portion of the transparent insulation film having a second thickness (D2) smaller than the first thickness.

In accordance with the LCD device of the present invention and a LCD device manufactured by the method of the present invention, the configuration wherein the transparent insulation film has a smaller thickness at the location in contact with the second electrode intensifies the electric field applied from the first electrode and the second electrode to the LC layer through the transparent insulation film, without a significant reduction in the withstand voltage of the transparent insulation film, and reduces the range of variation in the electric field applied to the LC layer, thereby suppressing the flicker or residual image of the LCD device.

The above and other objects, features and advantages of the present invention will be more apparent from the following description, referring to the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

FIGS. 1A and 1B are a sectional views of an IPS-mode LCD device according to a first embodiment of the present invention, taken along a row direction and a column direction, respectively, of an array of pixels.

FIG. 2 is a top plan view of a pixel in the LCD device of the first embodiment.

FIGS. 3A to 3C are sectional views of the LCD device of the first embodiment in consecutive steps of fabrication thereof.

FIG. 4 is a top plan view of a LCD device according to a second embodiment of the present invention.

FIGS. 5A and 5B are sectional views of a LCD device according to a third embodiment of the present invention, taken along a row direction and a column direction, respectively.

FIGS. 6A and 6B are sectional views of the LCD device of the third embodiment in consecutive steps of fabrication thereof.

FIG. 7 is a sectional view of a conventional LCD device.

FIG. 8A is a top plan view of the conventional LCD device, and FIG. 8B is a top plan view of another conventional LCD device.

PREFERRED EMBODIMENT OF THE INVENTION

Now, the present invention is more specifically described with reference to accompanying drawings, wherein similar constituent elements are designated by similar reference numerals throughout the drawings. FIGS. 1A and 1B show an active-matrix IPS-mode LCD device according to the first embodiment of the present invention.

The LCD device, generally designated by numeral 100, includes an array of pixels 101, one of which is shown in FIGS. 1A and 1B. The LCD device 100 includes a TFT substrate 10 and a counter substrate 20 sandwiching therebetween a LC layer 30 including LC molecules 31 therein. The LCD device 100 is disposed in front of a backlight source (not shown), with a counter substrate 20 being disposed on the front side of the LC layer 30. Each pixel 101 has a light switching function for transmitting the backlight 45 emitted by the backlight source. The light switching function of each pixel 101 is controlled by a corresponding TFT (not shown) formed on the TFT substrate 10. The counter substrate 20

mounts thereon color filters 23 for respective pixels and a black matrix 22 defining a light-shield area 102.

The TFT substrate 10 includes a glass substrate body 11. A plurality of scanning lines 12 and a plurality of common lines 13 extend on the glass substrate body 11 in the row direction within the light-shield area 102, and are covered by a gate insulation film 14. A plurality of data lines 15 extend on the gate insulation film 14 in the column direction within the light-shield area 102. Pixel electrodes 16 are also formed from the conductive layer configuring the data lines 15.

The scanning lines 12, common lines 13, data lines 15 and pixel electrodes 16 are made of a metallic material. The data lines 13 and pixel electrodes 16 should have a suitable thickness in view of a flat top surface of the overlying insulation films and a lower electric resistance thereof, and preferably have a thickness of 150 to 250 nm, (e.g., 200 nm).

A passivation film 17 covers the data lines 15 and pixel electrodes 16 on the gate insulation film 14. On the passivation film 17, patterned organic stripes 18 having a relatively large thickness extend in the column direction while overlapping the data lines 15 as viewed normal to the substrate surface. Common electrodes 19 made of a transparent conductive material, e.g., indium-tin-oxide (ITO), cover the patterned organic stripes 18 and the passivation film 17.

ITO has a relatively higher electric resistivity compared to the metallic material. Thus, the metallic material configuring the common lines 13 reduces the overall resistance of the common electrodes 19 and the common lines 13, thereby suppressing a delay in the signal transfer. The patterned organic stripes 18 may have a thickness as large as around 1.5 μm reduce a coupling capacitance between the data lines 15 and the common electrodes 19. The patterned organic stripes may have a thickness of 0.3 to 3 μm .

The counter substrate 20 includes a glass substrate body 21, on which a portion of the black matrix 22 extends in the row direction to configure part of the light-shield area 102, wherein the scanning lines 12 and the common lines 13 extend. Color filters 23 cover the area of the pixels 201 and part of the black matrix 22. Edges of the adjacent color filters 23 overlap each other to configure part of the light-shield area 102 extending in the column direction. An overcoat film 24 is formed on the black matrix 22 and color filters 23.

Orientation films 41, 42 are formed on the outermost surface of the TFT substrate 10 and counter substrate 20, respectively, opposing the LC layer 30. The orientation film 41, 42 are subjected to rubbing in the directions parallel to each other before fabrication of the LCD device 100, whereby the LC molecules 31 in the LC layer 30 are homogeneously oriented in the rubbing direction in the initial state thereof. A pair of polarizing films 43, 44 are disposed in cross-nicols to one another on the light-incident side of the TFT substrate 10 and the light-emitting side of the counter substrate 20, respectively. The polarizing film 43 on the TFT substrate 10 has a light absorption axis coinciding with the direction of the initial orientation of the LC molecules 31.

FIG. 2 shows the arrangement of the electrodes in each pixel 201. FIGS. 1A and 1B correspond to sectional views taken along lines Ia-Ia and Ib-Ib, respectively, in FIG. 2. Each scanning line 12 and each common line 13 extend in the row direction of the array of pixels between adjacent pixels 101. Each data line 15 extends in the column direction between adjacent pixels 101.

In the vicinity of each intersection between the scanning lines 12 and data lines 15, there is provided a TFT 51 for driving a corresponding pixel 101. The TFT 51 includes an island semiconductor layer 52, source/drain electrodes 53, 54 and a part of scanning lines 12 configuring the gate electrode.

The source electrode **53** is connected to the pixel electrode **16**, the drain electrode **54** is connected to a corresponding data line **15**. The common lines **13** are connected to the overlying common electrodes **19** via plugs **55** formed in the passivation film **17** and gate insulation film **14**.

The pixel electrode **16** includes a lead portion **16a** extending from the source electrode **53**, and a plurality of branch lines **16b** extending parallel to one another from the lead portion **16a** within the pixel **101**. The common electrode **19** includes a lead portion **19a** common to a row of pixels **101**, and a plurality of branch lines **19b** extending parallel to one another from the lead portion **19a** within the pixel **101**. The lead portion **16a**, **19a** and corresponding branch lines **16b**, **19b** configure a comb shape. The branch lines **16b** and the branch lines **19a** apply therebetween a corresponding part of the LC layer **30** with a lateral electric field. Some of the branch lines **19b** overlap the data lines **15** as viewed normal to the substrate surface to thereby shield the electric field generated by the data lines **15**.

The lead portion **16a** of the pixel electrode **16** overlaps part of the common line **13** as viewed normal to the substrate surface, whereas the lead portion **19a** of the common electrode **19** overlaps part of the scanning line **12** and common line **13** as viewed normal to the substrate surface. The lead portion **16a** of the pixel electrode **16** involves a coupling capacitor in connection with the underlying common line **13** and the overlying lead portion **19a** of the common electrode **19**, the coupling capacitor having a charge storage function.

The orientation films **41**, **42** have a rubbing direction **32**, which coincides with the column direction of the pixels **101**. The data lines **15**, branch lines **16b** of the pixel electrodes **16**, and branch lines **19b** of the common electrodes **19** extend in a **5** direction having a specific angle with respect to the rubbing direction **32**, and have a symmetric structure with respect to the central line thereof in the column direction. More specifically, those electrode lines extend in the direction a specific angle deviated from the rubbing direction **32** in the counter-clockwise direction in the first half area **103** of the pixel **101** near the TFT **51**, whereas those electrode lines extend in the direction the specific angle deviated from the rubbing direction **32** in the clockwise direction in the second half area **104** of the pixel **101** far from the TFT **51**. The edge **56** of the branch lines **16b** of the pixel electrode **16** overlaps the lead portion **19a** of the common electrode **19** as viewed in the direction normal to the substrate surface.

In an initial state of the pixel **101** wherein no voltage is applied between the pixel electrode **16** and the common electrode **19**, the LC molecules **31** are oriented parallel to the absorption axis of the polarizing film **43** on the TFT substrate **10**, whereby the light incident onto the TFT substrate **10** cannot pass through the LC layer **30** toward the counter substrate **20**.

Upon application of a specific voltage between the pixel electrode **16** and the common electrode **19** by the function of the TFT **51**, the LC molecules **31** in a corresponding portion are rotated in a plane parallel to the substrate surface due to the lateral electric field generated by the specific voltage. The light incident onto the TFT substrate **10** is allowed to pass through the LC layer **30** toward the counter substrate **20** due to the birefringence of the LC layer **30**, and is controlled for the light intensity of the transmitted light, by controlling the magnitude of the 10 voltage and thus the rotational angle of the LC molecules **31**.

The symmetric structure of the electrode lines in the pixel **101** generates a symmetric electric field with respect to the central line, thereby rotating the LC molecules **31** in opposite rotational directions in the first half area **103** and second half

area **104** of the pixel **101**. In this rotation, both the first and second half areas **103**, **104** compensate each other in the optical characteristic of the transmitted light, to improve the optical characteristic of the LCD device **100** as observed in a slanted viewing direction.

Referring again to FIGS. **1A** and **1B**, in the LCD device **100** of the present embodiment, the portion of the passivation film **17** on which the common electrode **19** is formed has a thickness (**D1**) of 300 nm, and the other portion of the passivation film **17** has a thickness (**D2**) of 100 nm. The larger-thickness portion of the passivation film **17** provides a higher withstand voltage between the pixel electrode **16** and the common electrode **19**. The smaller-thickness portion of the passivation film **17** intensifies the lateral electric field applied to the LC layer **30**, to thereby reduce the voltage to be applied between the pixel electrode **16** and the common electrode **19** and thus reduce the power dissipation of the LCD device **100**. Numeral **61** shown in FIGS. **1A** and **1B** depicts a portion of a transparent insulation film (silicon nitride film) removed in a fabrication process to configure the 10 passivation film **17** having different thicknesses **D1** and **D2**.

In the LCD device **100** of the present embodiment, the smaller-thickness portion of the passivation film **17** reduces the distance between the pixel electrode **16** and the LC layer **30**, thereby reducing the range of variation in the electric field applied to the LC layer **30**. This reduces variation of the electric charge stored in the interface between the orientation film **41** and the LC layer **30** among the pixels, thereby suppressing flicker and residual image.

According to the study by the inventor, the relationship 20 between film thicknesses **D1** and **D2** satisfying $D2 < D1 - 40$ (nm) assured a stable withstand voltage between the pixel electrode **16** and the common electrode **19**, an effectively reduced voltage within the passivation film **17**, and a reduced range of variation of the electric field in the LC layer **30** among the pixels. It is preferable that **D1** be 150 nm or above, and that **D2** be 100 nm or below for achieving a reduced voltage within the passivation film **17** and a reduced range of variation of the electric field in the LC layer **30** among the pixels.

A fabrication process for the LCD device of FIGS. **1A** and **1B** will be described hereinafter. A metallic film is deposited on a glass substrate body **11** by sputtering, followed by patterning thereof to form data lines **12** and common lines **13** (refer to FIG. **1B**). The metallic film may be 10 made of chrome, for example.

A gate insulation film **14**, an undoped amorphous silicon film and an n-type amorphous silicon film are consecutively deposited using a plasma-enhanced chemical vapor deposition (PECVD) technique to a thickness of 400 nm, 200 nm and 30 nm, respectively. Subsequently, a dry-etching process is conducted to pattern the amorphous silicon films to form island semiconductor layers **52** for respective TFTs **51** (FIG. **2**).

Thereafter, a metallic film is deposited on the island 20 semiconductor layers **52** and gate insulation film **14** by sputtering, followed by patterning thereof to configure data lines **15**, pixel electrodes **16**, source electrodes **53** and drain electrodes **54**. The metallic film may be made of chrome, for example.

Subsequently, a silicon nitride film is deposited on the data lines **15**, pixel electrodes **16**, source electrodes **53**, drain electrodes **54** and gate insulation film **14** to a thickness of 300 nm. A 1.5- μ m in-thick photosensitive acrylic film is then formed on the silicon nitride film by coating, exposed to light and developed using a developing solution to configure patterned organic stripes **18**.

Subsequently, through-holes are formed in the silicon nitride film **61** and gate insulation film **14** by using a selective etching technique. FIGS. **3A** to **3C** consecutively show subsequent steps of the fabrication. These figures correspond to the location of FIG. **1A**. As shown in FIG. **3A**, an ITO film **62** is then deposited on the silicon nitride film **61** and within the through-holes by sputtering. A photoresist mask pattern **63** is then formed on the ITO film **62** by using a known photolithographic and etching technique, and used for patterning the ITO film **62** to configure plugs filling the through-holes and common electrodes **19**, as shown in FIG. **3B**.

Thereafter, a top portion of the silicon nitride film **61** **20** having a thickness of 200 nm is removed by etching using the resist mask **63** as an etching mask, as shown in FIG. **3C**. This step provides a passivation film **17** having a thickness (**D1**) of 300 nm at the portion in contact with the common electrode **19**, and a thickness (**D2**) of 100 nm at the other portion. The resist mask **63** is then removed to achieve the TFT substrate **10**.

Separately from the TFT substrate **10**, a counter substrate **20** is formed by using a known technique. Both the substrates **10**, **20** are then provided with respective orientation films **41**, **42**, which are subjected to a rubbing treatment in a specified direction. The resultant substrates **10**, **20** are then bonded together using a sealing member at the periphery of the substrates **10**, **20**, with spacers being sandwiched therebetween to form a gap. A LC material is then injected into the gap through an injection port to form a LC layer **30**, and the injection port is then plugged.

Polarizing films **41**, **42** are then bonded onto the light-incident surface of the TFT substrate **10** and the light-emitting surface of the counter substrate **20**. The polarizing film **43** on the TFT substrate **10** has a light-absorbing axis aligned with the initial orientation of the LC molecules **31**, and both the orientation films **43**, **44** are disposed in crossnicols with each other. Driver ICs and signal processing boards are then bonded onto the TFT substrate **10** for driving the TFTs, whereby the final structure of the LCD device of the present embodiment is obtained.

The above process uses the resist mask **63**, which is used for patterning the common electrodes **19**, during forming the different thicknesses of the passivation film **17**, thereby simplifying the fabrication process.

FIG. **4** shows, similarly to FIG. **2**, arrangement of electrodes in a pixel of a LCD device **105** according to a second embodiment of the present invention. In the LCD device **105** of the second embodiment, the branch lines **16b** of the pixel electrode **16** is made of an ITO film and overlies the lead portion **16a** made of a metallic film. Other configurations are similar to those of the first embodiment.

The transparent branch lines **16b** of the pixel electrode raises the opening ratio of the pixel, and thus improves the coefficient of utilization of the transmitted light, thereby increasing the luminance of the LCD device **105**.

In manufacture of the LCD device **105** of the second embodiment, the metallic film formed on the gate insulation film is patterned to configure the lead portion **16a** of the pixel electrodes excepting the branch lines **16b**. The branch lines **16b** are formed from ITO film overlying the lead portion **16a**.

FIGS. **5A** and **5B** show, similarly to FIGS. **1A** and **1B**, a LCD device **106** according to a third embodiment of the present invention. In the third embodiment, the portion of the passivation film **17** in contact with the pixel electrode **16** and the vicinity thereof has a thickness (**D2**) smaller than the thickness (**D1**) of the other portion of the passivation film **17** by an amount corresponding to the thickness of the pixel electrode **16**. This configuration provides a substantially flat

top surface to the passivation film **17**. Other configurations of the present embodiment are similar to those of the first embodiment.

The substantially flat top surface of the passivation film **17** improves the uniformity of the orientation of the LC molecules **31**, thereby improving the contrast ratio of the LCD device **106**.

In manufacture of the LCD device **106** of the third embodiment, as shown in FIG. **6A**, a resist mask **63** having an opening corresponding to the location of the common electrodes **19** and the vicinity thereof is formed on the silicon nitride film **61**. Subsequently, as shown in FIG. **6B**, an etching process is conducted using the resist mask **63** as an etching mask to selectively etch a portion of the silicon nitride film **61** corresponding to the opening by an amount corresponding to the thickness of the common electrodes **19**. Thus, the resultant silicon nitride film **61** has a substantially flat top surface.

Since the above embodiments are described only for 20 examples, the present invention is not limited to the above embodiments and various modifications or alterations can be easily made therefrom by those skilled in the art without departing from the scope of the present invention.

What is claimed is:

1. A liquid crystal display (LCD) device comprising a liquid crystal (LC) layer, and first and second substrates sandwiching therebetween said LC layer to define a plurality of pixels, said first substrate including a first electrode and a second electrode in each of said pixels to apply said LC layer with a lateral electric field, wherein: said first substrate mounts thereon a transparent insulation film; said first electrode is formed on a first surface of said transparent insulation film near said LC layer, said second electrode is formed on a second surface of said transparent insulation film far from said LC layer; and said transparent insulation film has a first thickness (**D1**) at a location in contact with said first electrode, and a second thickness (**D2**) smaller than said first thickness at a location in contact with said second electrode, wherein the following relationship holds: $D2 < D1 - 40$ (nm), and wherein the first substrate further comprises a substrate body, wherein a shortest distance between the first electrode and the substrate exceeds a distance between the LC layer and the substrate body.

2. The LCD device according to claim 1, wherein said transparent insulation film has a portion in contact with both said first electrode and said second electrode, wherein said first electrode and said second electrode at least partially overlap with said portion at least partially sandwiched therebetween, and said portion of said transparent insulation film has a thickness equal to or larger than said first thickness.

3. The LCD device according to claim 1, further comprising data lines for supplying data signals to said pixels, wherein said data lines extend on said second surface of said transparent insulation film, and overlap part of said first electrode as viewed normal to said first and second surfaces.

4. The LCD device according to claim 1, wherein said first surface of said transparent insulation film is a substantially flat surface.

5. The LCD device according to claim 1, wherein said transparent insulation film further comprises a third portion in contact with neither the first electrode, nor the second electrode, wherein said third portion spans a thickness of said transparent insulation film, and wherein the thickness of said transparent insulation film at said third portion is less than said first thickness.

6. The LCD device according to claim 1, further comprising an orientation film applied uniformly on each side of the LC layer.

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7. The LCD device according to claim 1, wherein the first substrate further comprises a substrate body; and a second insulation film applied between the substrate body and the second electrode.

8. A liquid crystal display (LCD) device comprising a liquid crystal (LC) layer, and first and second substrates sandwiching therebetween said LC layer to define a plurality of pixels, said first substrate including a first electrode and a second electrode in each of said pixels to apply said LC layer with a lateral electric field, wherein: said first substrate mounts thereon a transparent insulation film; said first electrode is formed on a first surface of said transparent insulation

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film near said LC layer, said second electrode is formed on a second surface of said transparent insulation film far from said LC layer; and said transparent insulation film has a first thickness (D1) at a location in contact with said first electrode, and a second thickness (D2) smaller than said first thickness at a location in contact with said second electrode, wherein the first substrate further comprises a substrate body, wherein a shortest distance between the first electrode and the substrate exceeds a distance between the LC layer and the substrate body.

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专利名称(译)	面内切换模式液晶显示装置		
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摘要(译)

IPS模式LCD装置包括TFT基板和夹在其间的LC层的相对基板。每个像素包括由形成在TFT基板上的钝化膜覆盖的像素电极，以及形成在钝化膜的顶表面上的公共电极。钝化膜在与公共电极接触的部分处具有第一厚度，并且与像素电极接触的部分处具有小于第一厚度的第二厚度，从而具有钝化膜的平坦顶表面。

